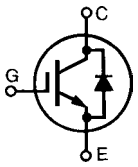
HiPerFAST™ IGBT with Diode

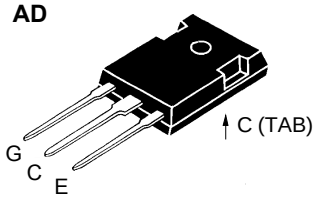
IXGH 24N60BU1

V_{CES} = 600 V
I_{C25} = 48 A
$V_{CE(sat)}$ = 2.3 V
t_{fi} = 80 ns



Symbol	Test Conditions	Maximum Ratings	
V_{CES}	T_J = 25°C to 150°C	600	V
V_{CGR}	T_J = 25°C to 150°C; R_{GE} = 1 MΩ	600	V
V_{GES}	Continuous	±20	V
V_{GEM}	Transient	±30	V
I_{C25}	T_C = 25°C	48	A
I_{C90}	T_C = 90°C	24	A
I_{CM}	T_C = 25°C, 1 ms	96	A
SSOA (RBSOA)	V_{GE} = 15 V, T_{VJ} = 125°C, R_G = 22 Ω Clamped inductive load, L = 100 µH	I_{CM} = 48 @ 0.8 V_{CES}	A
P_C	T_C = 25°C	150	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
Maximum Lead and Tab temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	°C
M_d	Mounting torque	1.13/10	Nm/lb.in.
Weight		6	g

TO-247 AD



G = Gate C = Collector
E = Emitter TAB = Collector

Symbol	Test Conditions		Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
BV_{CES}	I_C = 750 µA, V_{GE} = 0 V		600			V
$V_{GE(th)}$	I_C = 250 µA, V_{CE} = V_{GE}		2.5		5.5	V
I_{CES}	V_{CE} = 0.8 • V_{CES} V_{GE} = 0 V	T_J = 25°C T_J = 125°C			500 8	µA mA
I_{GES}	V_{CE} = 0 V, V_{GE} = ±20 V				±100	nA
$V_{CE(sat)}$	I_C = I_{C90}, V_{GE} = 15 V				2.3	V

Features

- High frequency IGBT and antiparallel FRED in one package
- High current handling capability
- 3rd generation HDMOS™ process
- MOS Gate turn-on
  - drive simplicity

Applications

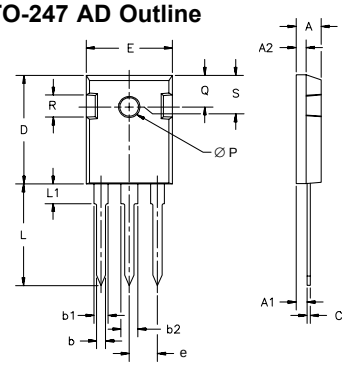
- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies

Advantages

- Space savings (two devices in one package)
- High power density
- Suitable for surface mounting
- Switching speed for high frequency applications
- Easy to mount with 1 screw (insulated mounting screw hole)

Symbol	Test Conditions	Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
g_{fs}	$I_C = I_{C90}$; V_{CE} = 10 V, Pulse test, t ≤ 300 µs, duty cycle ≤ 2 %	9	13		S
C_{ies}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz		1500		pF
C_{oes}			175		pF
C_{res}			40		pF
Q_G	$I_C = I_{C90}$, V_{GE} = 15 V, V_{CE} = 0.5 V_{CES}		90	120	nC
Q_{GE}			11	15	nC
Q_{GC}			30	40	nC
$t_{d(on)}$	**Inductive load, T_J = 25°C**		25		ns
t_{ri}	$I_C = I_{C90}$, V_{GE} = 15 V, L = 100 µH,		15		ns
E_{on}	V_{CE} = 0.8 V_{CES}, $R_G = R_{off}$ = 10 Ω		0.6		mJ
$t_{d(off)}$	Remarks: Switching times may		150	200	ns
t_{fi}	increase for V_{CE} (Clamp) > 0.8 • V_{CES},		80	150	ns
E_{off}	higher T_J or increased R_G 24N60BU1		0.8		mJ
$t_{d(on)}$	**Inductive load, T_J = 125°C**		25		ns
t_{ri}	$I_C = I_{C90}$, V_{GE} = 15 V, L = 100 µH		15		ns
E_{on}	V_{CE} = 0.8 V_{CES}, $R_G = R_{off}$ = 10 Ω		0.8		mJ
$t_{d(off)}$			250		ns
t_{fi}			100		ns
E_{off}	24N60BU1		1.4		mJ
R_{thJC}				0.83	K/W
R_{thCK}			0.25		K/W

TO-247 AD Outline

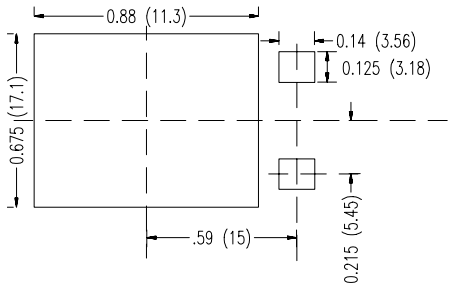


Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.7	5.3	.185	.209
A_1	2.2	2.54	.087	.102
A_2	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b_1	1.65	2.13	.065	.084
b_2	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15 BSC		242 BSC	

Reverse Diode (FRED)

Symbol	Test Conditions	Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
V_F	$I_F = I_{C90}$, V_{GE} = 0 V, Pulse test, t ≤ 300 µs, duty cycle d ≤ 2 %			1.6	V
I_{RM}	$I_F = I_{C90}$, V_{GE} = 0 V, -di_F/dt = 240 A/µs		10	15	A
t_{rr}	V_R = 360 V T_J = 125°C		150		ns
	I_F = 1 A; -di/dt = 100 A/µs; V_R = 30 V T_J = 25°C		35	50	ns
R_{thJC}				1	K/W

Min. Recommended Footprint (Dimensions in inches and (mm))



IXYS reserves the right to change limits, test conditions, and dimensions.

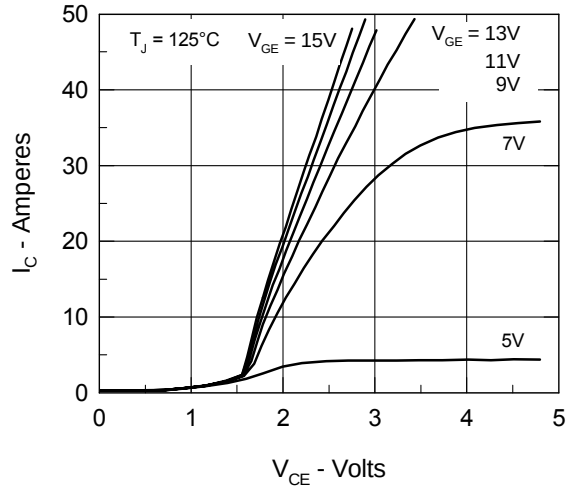


Fig. 1. Saturation Voltage Characteristics

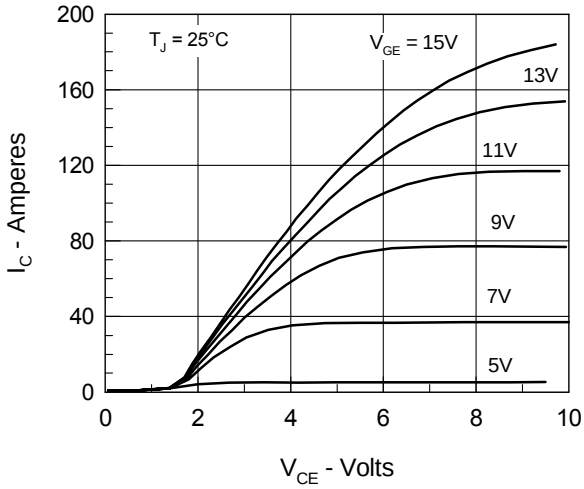


Fig. 2. Extended Output Characteristics

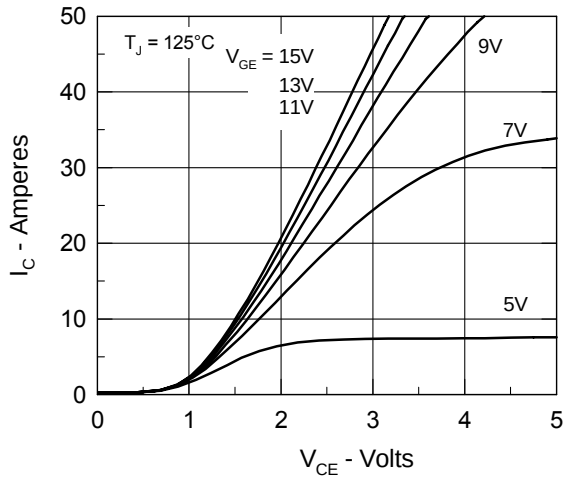


Fig. 3. Saturation Voltage Characteristics

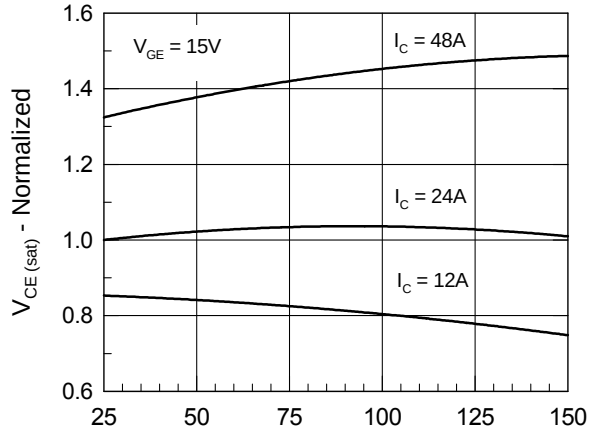


Fig. 4. Temperature Dependence of $V_{CE(sat)}$

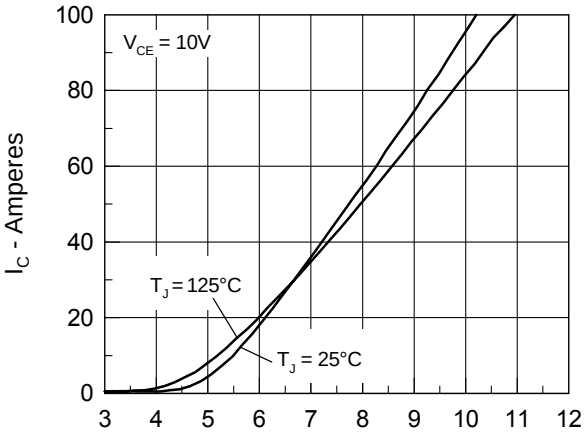


Fig. 5. Admittance Curves

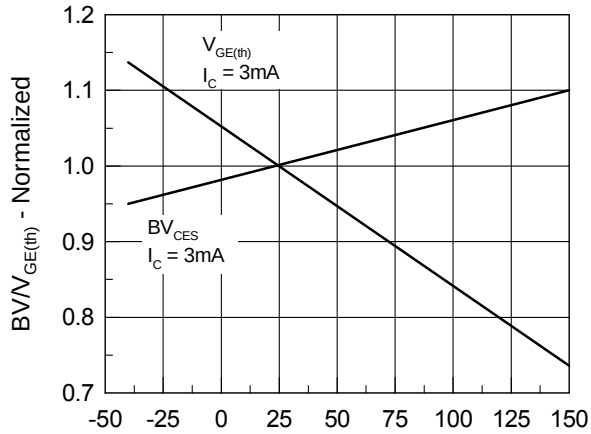


Fig. 6. Temperature Dependence of BV_{DSS} & $V_{GE(th)}$

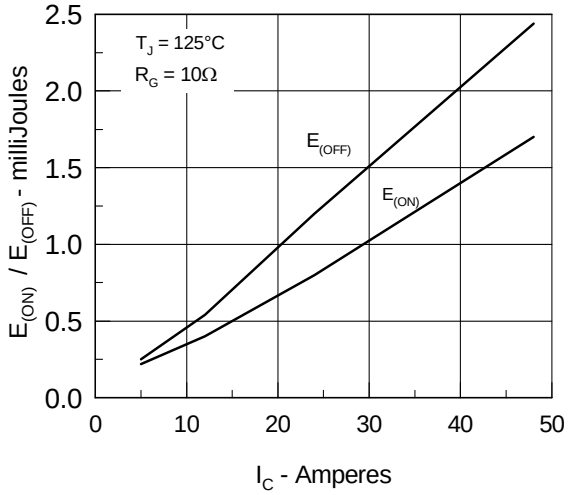


Fig. 7. Dependence of tfi and E_{OFF} on I_C.

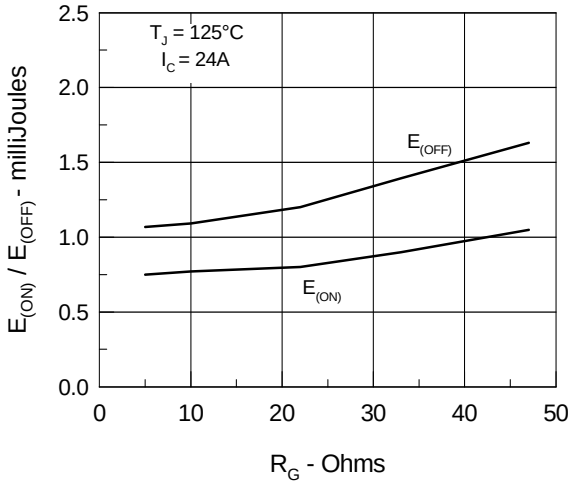


Fig. 8. Dependence of tfi and E_{OFF} on R_G.

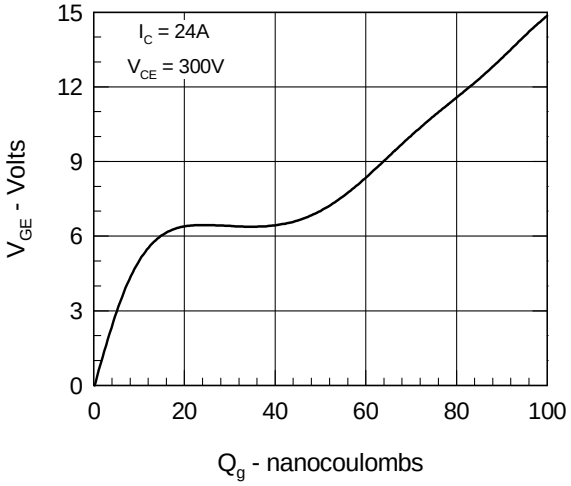


Fig. 9. Gate Charge

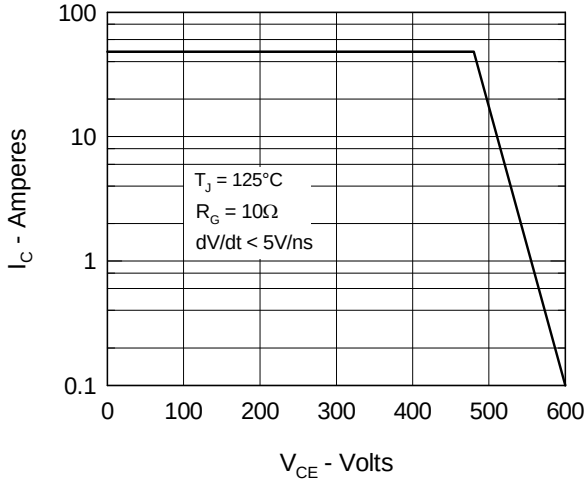


Fig. 10. Turn-off Safe Operating Area

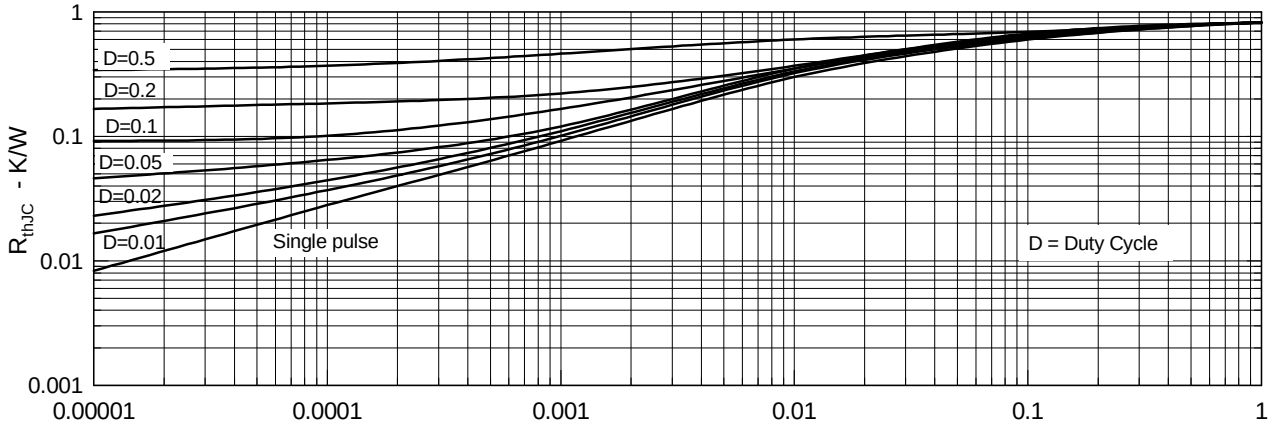


Fig. 11. Transient Thermal Resistance

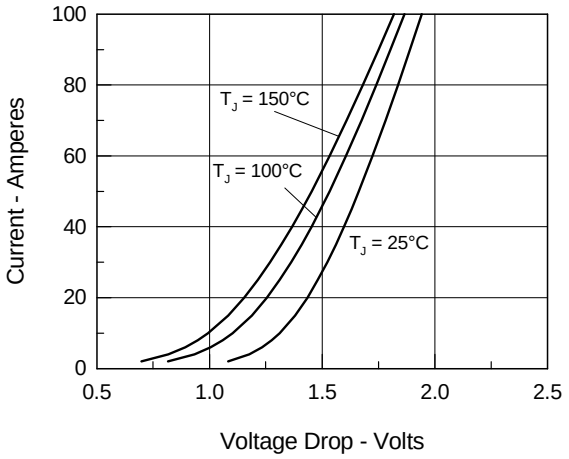


Fig.12 Maximum Forward Voltage Drop

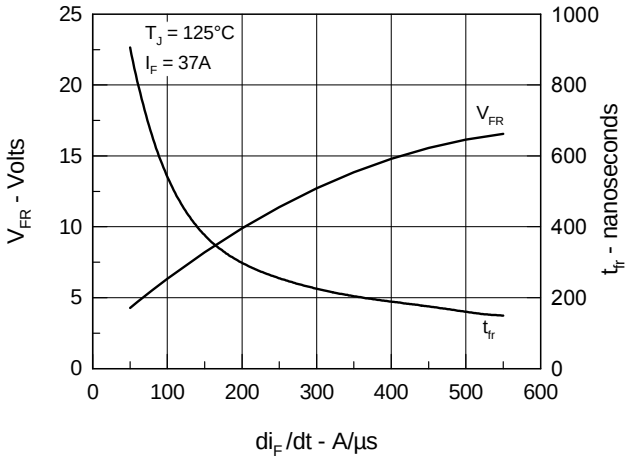


Fig.13 Peak Forward Voltage V_{FR} and Forward Recovery Time t_{FR}

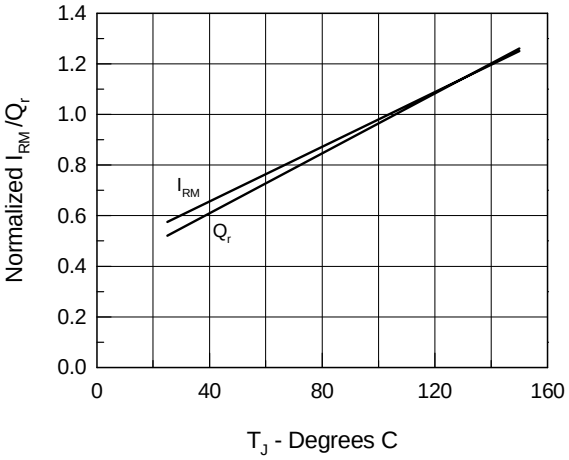


Fig.14 Junction Temperature Dependence off I_{RM} and Q_r

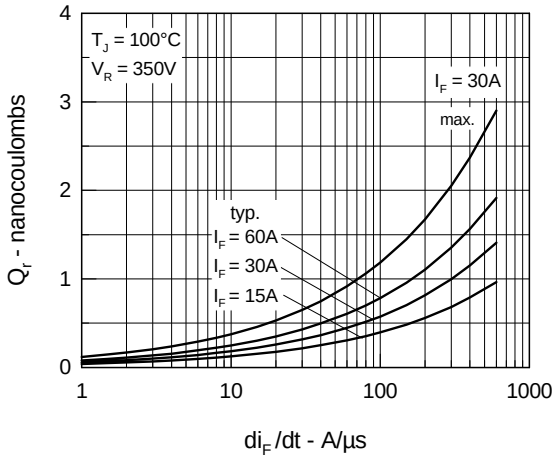


Fig.15 Reverse Recovery Chargee

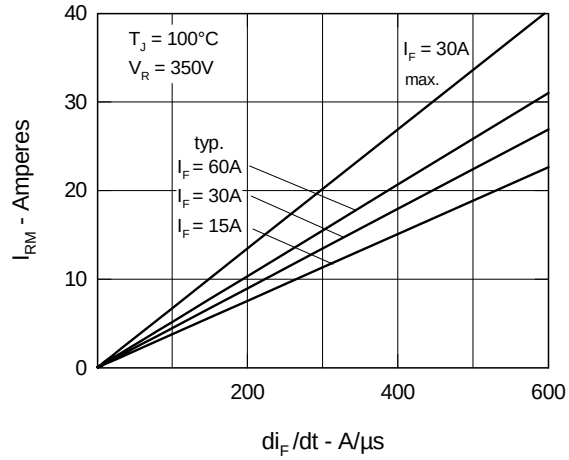


Fig.16 Peak Reverse Recovery Current

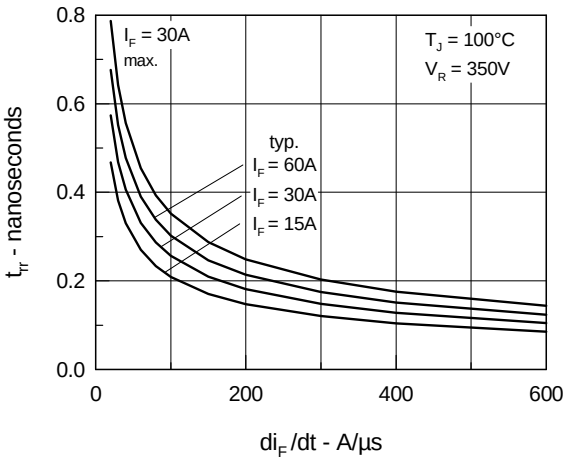


Fig.17 Reverse Recovery Time

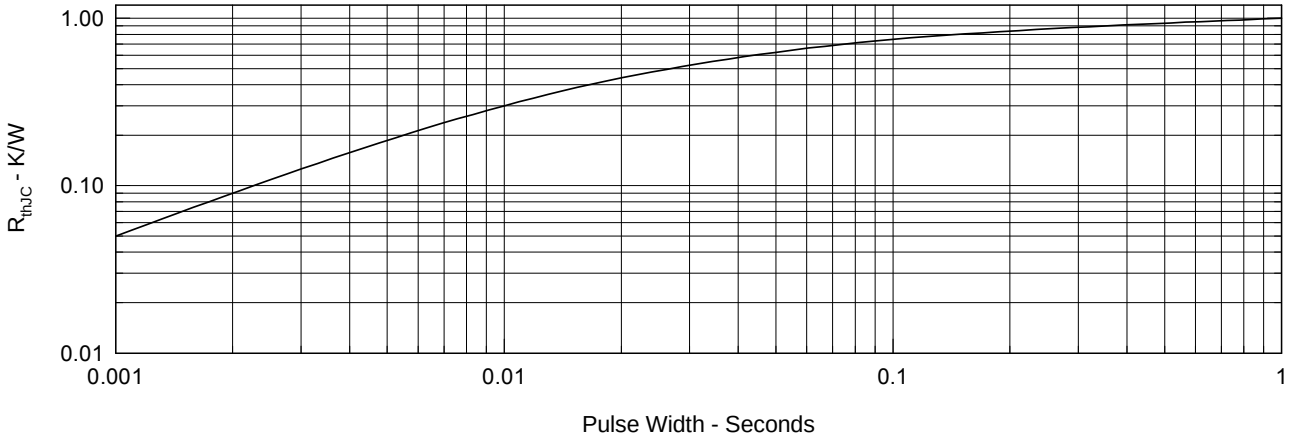


Fig.18 Diode Transient Thermal resistance junction to case